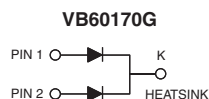
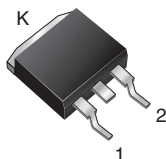


# Dual High Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.50\text{ V}$  at  $I_F = 5\text{ A}$

TMBS®  
TO-263AB



## FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT

## TYPICAL APPLICATIONS

For use in high frequency DC/DC converters, switching power supplies, freewheeling diodes, OR-ing diode, and reverse battery protection.

## MECHANICAL DATA

**Case:** TO-263AB

Molding compound meets UL 94 V-0 flammability rating  
Base P/N-E3 - RoHS-compliant, commercial grade

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum

| PRIMARY CHARACTERISTICS      |                |
|------------------------------|----------------|
| $I_{F(AV)}$                  | 2 x 30 A       |
| $V_{RRM}$                    | 170 V          |
| $I_{FSM}$                    | 210 A          |
| $V_F$ at $I_F = 30\text{ A}$ | 0.72 V         |
| $T_J$ max.                   | 175 °C         |
| Package                      | TO-263AB       |
| Diode variations             | Common cathode |

| MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)                     |                |             |            |
|------------------------------------------------------------------------------------|----------------|-------------|------------|
| PARAMETER                                                                          | SYMBOL         | VB60170G    | UNIT       |
| Maximum repetitive peak reverse voltage                                            | $V_{RRM}$      | 170         | V          |
| Maximum average forward rectified current (fig. 1)                                 | $I_{F(AV)}$    | 60          | A          |
|                                                                                    |                | 30          |            |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load | $I_{FSM}$      | 210         | A          |
| Voltage rate of change (rated $V_R$ )                                              | $dV/dt$        | 10 000      | V/ $\mu$ s |
| Operating junction and storage temperature range                                   | $T_J, T_{STG}$ | -40 to +175 | °C         |

| <b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted) |                      |                                     |      |      |               |
|------------------------------------------------------------------------------------------------|----------------------|-------------------------------------|------|------|---------------|
| PARAMETER                                                                                      | TEST CONDITIONS      | SYMBOL                              | TYP. | MAX. | UNIT          |
| Instantaneous forward voltage per diode                                                        | $I_F = 5\text{ A}$   | $V_F^{(1)}$                         | 0.65 | -    | V             |
|                                                                                                | $I_F = 15\text{ A}$  |                                     | 0.78 | -    |               |
|                                                                                                | $I_F = 30\text{ A}$  |                                     | 0.87 | 1.02 |               |
|                                                                                                | $I_F = 5\text{ A}$   | $T_A = 125\text{ }^{\circ}\text{C}$ | 0.50 | -    |               |
|                                                                                                | $I_F = 15\text{ A}$  |                                     | 0.62 | -    |               |
|                                                                                                | $I_F = 30\text{ A}$  |                                     | 0.72 | 0.80 |               |
| Reverse current per diode                                                                      | $V_R = 136\text{ V}$ | $T_A = 25\text{ }^{\circ}\text{C}$  | 1.5  | -    | $\mu\text{A}$ |
|                                                                                                |                      | $T_A = 125\text{ }^{\circ}\text{C}$ | 2.5  | -    | mA            |
|                                                                                                | $V_R = 170\text{ V}$ | $T_A = 25\text{ }^{\circ}\text{C}$  | -    | 450  | $\mu\text{A}$ |
|                                                                                                |                      | $T_A = 125\text{ }^{\circ}\text{C}$ | 5    | 50   | mA            |

**Notes**

(1) Pulse test: 300  $\mu\text{s}$  pulse width, 1 % duty cycle

(2) Pulse test: Pulse width  $\leq 20\text{ ms}$ 

| <b>THERMAL CHARACTERISTICS</b> ( $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted) |                 |            |      |
|---------------------------------------------------------------------------------------------|-----------------|------------|------|
| PARAMETER                                                                                   | SYMBOL          | VB60170G   | UNIT |
| Typical thermal resistance                                                                  | $R_{\theta JC}$ | per diode  | 1.0  |
|                                                                                             |                 | per device | 0.7  |

| <b>ORDERING INFORMATION</b> (Example) |                |                 |              |               |               |
|---------------------------------------|----------------|-----------------|--------------|---------------|---------------|
| PACKAGE                               | PREFERRED P/N  | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| TO-263AB                              | VB60170G-E3/4W | 1.38            | 4W           | 50/tube       | Tube          |
| TO-263AB                              | VB60170G-E3/8W | 1.38            | 8W           | 800/reel      | Tape and reel |

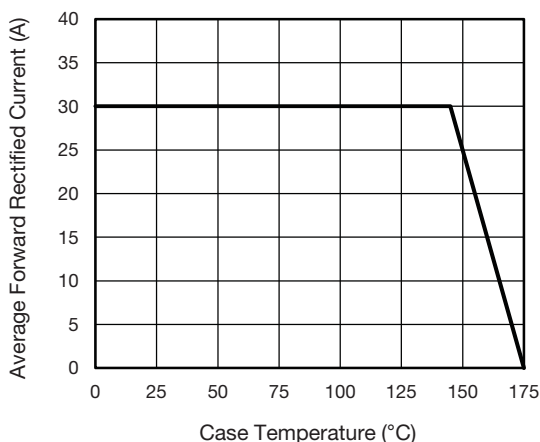
**RATINGS AND CHARACTERISTICS CURVES** ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise noted)


Fig. 1 - Maximum Forward Current Derating Curve

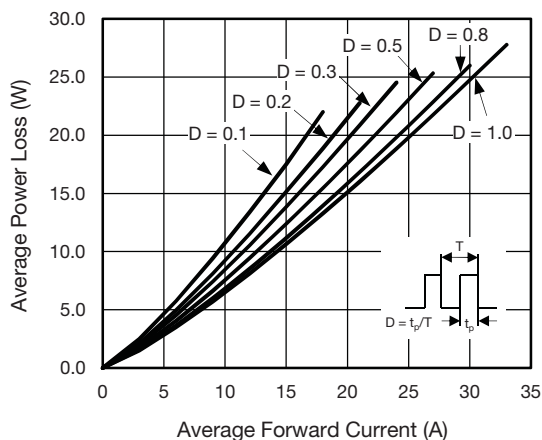


Fig. 2 - Forward Power Loss Characteristics Per Diode

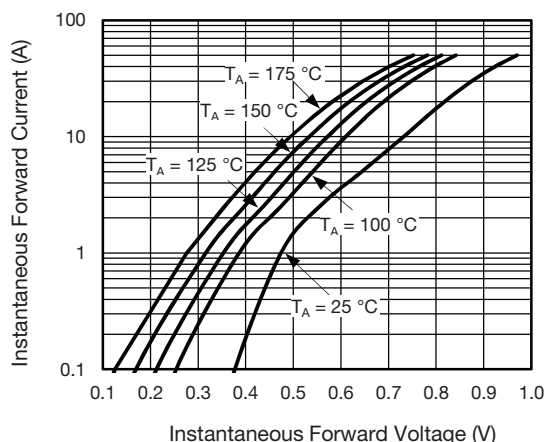


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

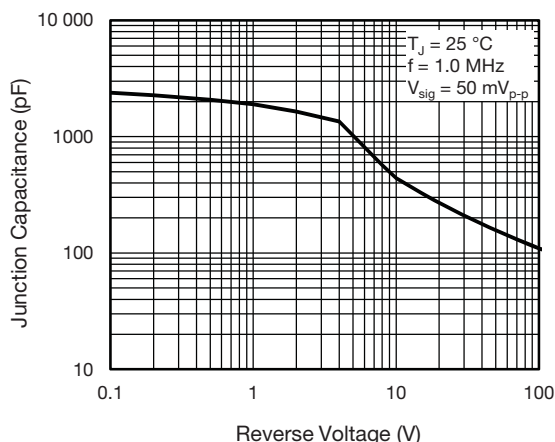


Fig. 5 - Typical Junction Capacitance Per Diode

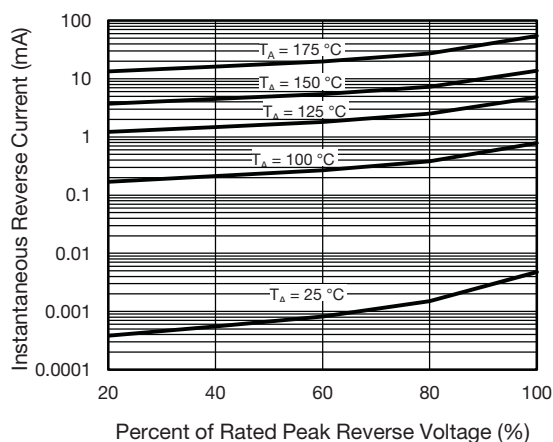


Fig. 4 - Typical Reverse Characteristics Per Diode

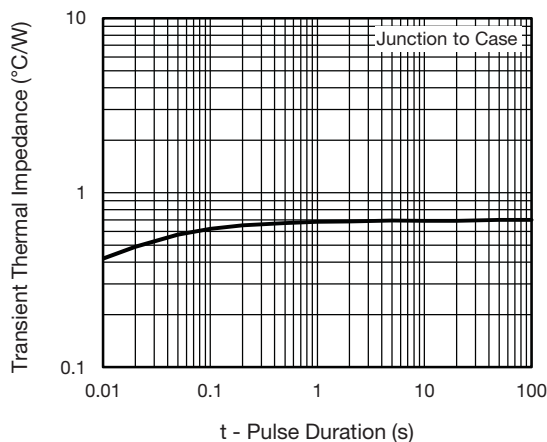
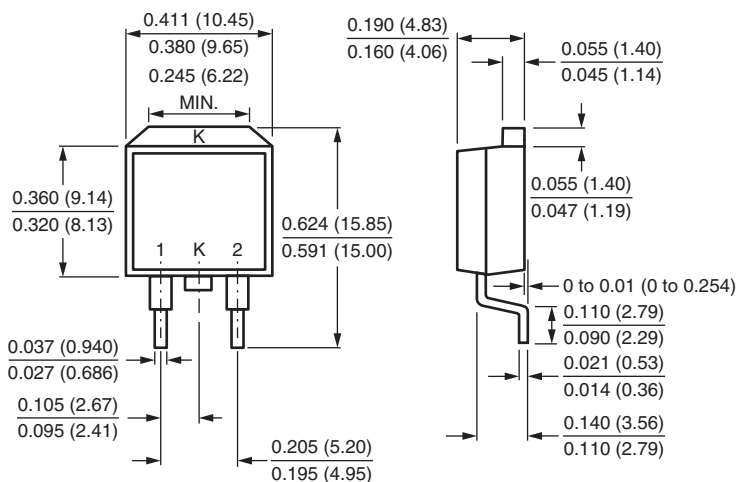


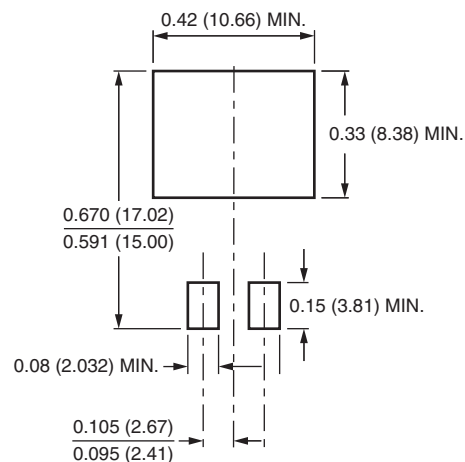
Fig. 6 - Typical Transient Thermal Impedance Per Diode

## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

### TO-263AB



### Mounting Pad Layout





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